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CARBIDES.JPAB.	2197
A-SIC.JPAB.	284
A-SICS	0
INSULAT$	0
INSULAT.JPAB.	183
((AMORPHOUS ADJ1 SLICON ADJ1 CARBIDE OR A-SIC) ADJ2 (INSULAT$ OR DILECTRIC$)).JPAB.	1

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Refine Search: `(amorphous adj1 slicon adj1 carbide or a-SiC) adj2 (insulat$ or dilectric$)` Clear

Search History

Today's Date: 9/22/2001

DB Name	Query	Hit Count	Set Name
JPAB	(amorphous adj1 slicon adj1 carbide or a-SiC) adj2 (insulat$ or dilectric$)	1	L4
USPT	(amorphous adj1 slicon adj1 carbide or a-SiC) adj2 (insulat$ or dilectric$)	0	L3
USPT	l1 and (amorphous adj1 slicon adj1 carbide or a-SiC) adj2 (insulat$ or dilectric$)	0	L2
USPT	floating adj1 gate and transistor	7082	L1

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Search Results - Record(s) 1 through 1 of 1 returned.

☐ 1. Document ID: JP 60123074 A

L4: Entry 1 of 1 File: JPAB Jul 1, 1985

PUB-NO: JP360123074A
DOCUMENT-IDENTIFIER: JP 60123074 A
TITLE: AMORPHOUS SILICON SOLAR CELL

PUBN-DATE: July 1, 1985

INVENTOR-INFORMATION:

NAME	COUNTRY
HAMA, TOSHIO	

US-CL-CURRENT: 136/244; 136/258
INT-CL (IPC): H01L 31/04

Full | Title | Citation | Front | Review | Classification | Date | Reference | Claims | KWIC | Draw. Desc | Image

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NAME	COUNTRY
HAMA, TOSHIO	

ASSIGNEE-INFORMATION:

NAME	COUNTRY
FUJI ELECTRIC CORP RES & DEV LTD	N/A

APPL-NO: JP58231798
APPL-DATE: December 8, 1983

US-CL-CURRENT: 136/244; 136/258
INT-CL (IPC): H01L 31/04

ABSTRACT:

PURPOSE: To shorten a manufacturing process for an insulating layer to a metallic substrate for an a-Si solar cell element formed on the substrate, and to reduce manufacturing cost by using an amorphous silicon carbide (a-SiC) layer as the insulating layer.

CONSTITUTION: A plurality of regions of insulating layers 2 consisting of a-SiC are shaped on a metallic substrate 1 while being mutually separated, N type a-Si layers 3 functioning as one electrodes are laminated on a plurality of the regions, I type a-Si layers 4 on regions, in which one parts of the N type layers are removed, and P type a-Si layers 5 on the layers 4 in succession, thus forming active layers 10 for mutually separated solar cell elements. The active layers 10, the outer circumferential surfaces of the insulating layers 2 and the exposed surfaces of the metallic substrate 1 are coated with an insulating film 6 consisting of a substance such as silicon oxide. The solar cell elements adjoining in succession are connected in series by forming transparent electrode layers 7 connecting sections 71 on the surfaces of the P type layers for each solar cell element and sections 72 on the exposed surfaces of the N type layers for adjacent elements. The active layers 10 may be laminated in orer of P types, I types and N types from the insulating layers 2 sides.